RADIANT TECHNOLOGIES PATENT LIST.

Patent #. Title :

1. 6.505.137 Method for operating a test system.
2. 6.459.137 Method for constructing ferroelectric capacitors on integrated circuit substrates.
3. 6.417.110 Method for constructing heat resistant electrode structures on silicone substrates.
4. 6.225.654 Static ferroelectric memory transistor having improved data retention.
5. 6.194.751 Ferroelectric based memory devices utilizing low Curie point ferroelectrics and encapsulation.
6. 6.121.648 Ferroelectric based memory devices utilizing hydrogen getters and recovery annealing.
7. 6.117.688 Method for constructing ferroelectric based capacitors for use in memory systems.
8. 6.074.885 Lead titanate isolation layers for use in fabricating PZT-based capacitors and similar structures.
9. 6.066.868 Ferroelectric based memory devices utilizing hydrogen barriers and getters.
10. 5.977.577 Ferroelectric based memory devices utilizing low Curie point ferroelectrics and encapsulation
11. 5.963.466 Ferroelectric memory having a common plate electrode.
12. 5.892.255 Ferroelectric based capacitor for use in memory systems and method for fabricating the same.
13. 5.872.739 Sense amplifier for low read-voltage memory cells.
14. 5.804.850 Ferroelectric based capacitor cell for use in memory systems.
15. 5.757.042 High density ferroelectric memory with increased channel modulation and double word ferroelectric memory cell for constructing the same.
16. 5.679.969 Ferroelectric based capacitor for use in memory systems and method for fabricating the same.
17. 5.614.438 Method for making LSCO stack electrode.
18. 5.593.914 Method for constructing ferroelectric capacitor-like structures on Silicone Dioxide.
19. 5.453.347 Method for constructing ferroelectric capacitors on integrated circuit substrates.
20. 5.440.173 High–temperature electrical contact for making contact to ceramic materials and improved circuit element using the same.
21. 5.240.428 Infra-Red sensing array.
22. 5.242.534 Platinum lift-off process.
23. 5.239.399 Electrical-optical interface device.
24. 5.232.747 Platinum –Aluminum connection system.
25. 5.212.620 Method for isolating SiO.sub.2 layers from PZT.PLZT and Platinum layers.
26. 5.179.533 Read/Write optical memory.
27. 5.164.808 Platinum electrode structure for use in conjunction with ferroelectric materials.
28. 5.119.329 Memory cell based on ferroelectric non- volatile variable resistive element.
29. 5.109.156 Light actuated optical logic device.
30. 5.078.478 Light actuated optical switching device.
31. 5.070.385 Ferroelectric non-volatile variable resistive element.
32. 5.051.950 Read/Write optical memory.
33. 5,314,087 Thermal Reflective Packaging System (1994)
34. 5,638,979 Thermal Reflective Packaging System (1997)
35. 7,990,749 Method for Constructing Heat Resistant Electrodes Structure on Silicone Substrates.
36. 8,310,856 Ferroelectric Memories Based on Arrays of Autonomous Memory Bits.
37. 8,565,000 Variable Impedance Circuit Controlled By a Ferroelectric Capacitor.
38. 8,760,907 B2 Analog Memories Utilizing Ferroelectric Capacitors.
39. 8,797.0603B2 Analog Memories Utilizing Ferroelectric Capacitors.
40. 8,824,186 B2 Embedding *Non-Volatile Memory Circuit for Implementing Logic Functions Across Fields of Power Disruption.*
41. *5,646,743 Japan Analog* Memories Utilizing Ferroelectric Capacitors.
42. 8,942,022 Embedding Non-Volatile Memory Circuit for Implementing Logic Functions Across Fields of Power Disruption.
43. 5,748,164 Japan Analog Memories Utilizing Ferroelectric Capacitors.
44. 9,106,218 Embedding *Non-Volatile Memory Circuit for Implementing Logic Functions Across Fields of Power Disruption.*
45. *8,964,446 B2* Analog Memories Utilizing Ferroelectric Capacitors.
46. 9,269,146 B2 Non-Volatile Counter Utilizing a Ferroelectric Capacitor.
47. Cert# 193276. Chinese Invention Patent Issuance: ZL 2011 8 0035995 . Ferroelectric Memories Based on Arrays of Autonomous Memory Bits.
48. 54886- China Chinese Invention Patent Issuance: ZL 2010 8 0068179.4 . Variable Impedance Circuit Controlled By a Ferroelectric Capacitor.
49. 9,324,405 CMOS Analog Memories Utilizing Ferroelectric Capacitors Related Apllications.